



型号：SLS60N02

N-CHANNEL MOSFET in a TO-252 Plastic Package.

主要特性/Features

$V_{DS}=20V$ $I_D=60A$

$R_{DS(ON)} < 5.8m\Omega @ V_{GS}=4.5V$

$R_{DS(ON)} < 7.5m\Omega @ V_{GS}=2.5V$

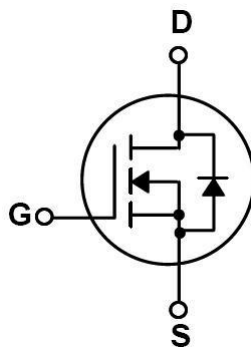
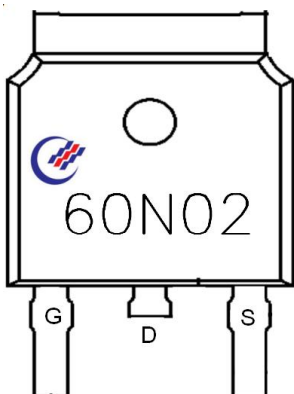
应用/Application

Battery protection

Load switch

Uninterruptible power supply

印字/MARKING 等效电路/Equivalent Circuit



极限参数/Absolute Maximum Ratings (TA=25°C unless otherwise noted)

参数Parameter	符号Symbol	数值Value	单位Unit
Drain-Source Voltage	V_{DS}	20	V
Drain Current	$I_D(T_C=25^\circ C)$	60	A
Drain Current	$I_D(T_C=100^\circ C)$	42	A
Drain Current - Pulsed	I_{DM}	210	A
Gate-Source Voltage	V_{GSS}	± 12	V
Single Pulsed Avalanche Energy	E_{AS}	64	mJ
Power Dissipation	$P_D(T_C=25^\circ C)$	60	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

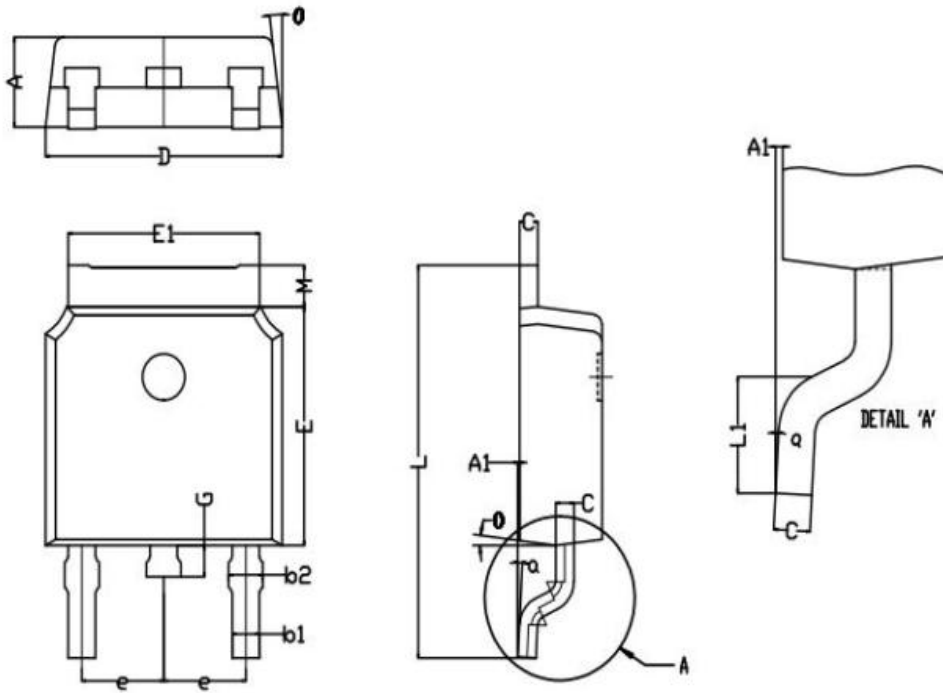


电性能参数/Electrical Characteristics (TA=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	20			V
I _{D(DeviceRef)}	Continuous Drain Current	T _J =25°C			60	A
R _{DS(on)}	Static Drain-to-Source On-Resistance	V _{GS} =4.5V, I _D =1A		3.5	5.5	mΩ
		V _{GS} =2.5V, I _D =1A		4.5	7	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.5	0.7	0.9	V
I _{DSS}	Drain-to-Source Leakage Current	V _{DS} =19.5V, V _{GS} =0V, T _J =25°C			100	nA
I _{GSS}	Gate-to-Source Leakage Current	V _{GS} =±12V			±100	nA
T _J , T _{STG}	Operating and Storage Temperature	-55 to 150°C Max				



成品外观尺寸/TO252-2L Package Information



Symbol	Dim in mm		
	Min	Nor	Max
A	2.25	2.30	2.35
L1	2.90	3.00	3.10
b1	0.71	0.76	0.81
b2	0.91	0.96	1.01
C	0.46	0.51	0.56
D	6.55	6.60	6.65
e	2.29 (BSC)		
E	6.05	6.10	6.15
E1	5.23	5.33	5.43
L	9.84	10.04	10.24
A1	0.00	0.05	0.10
M	1.01	1.06	1.11
G	0.70	0.80	0.90
Q	0°	5°	10°
Q	0°	3°	6°